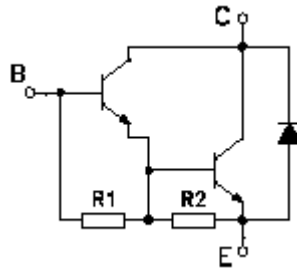


BU806FI

Silicon NPN Transistors



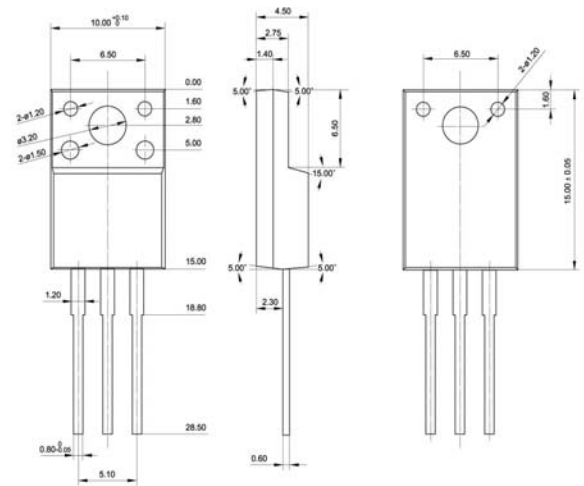
B C E

◆ Features

- . With TO-220F package
- . DARLINGTON
- . High voltage ,high current device for fast switching applications.

◆ Absolute Maximum Ratings Tc=25°C

SYMBOL	PARAMETER	RATING	UNIT
V _{CB0}	Collector to base voltage	400	V
V _{CEO}	Collector to emitter voltage	200	V
V _{EBO}	Emitter to base voltage	6	V
I _{CP}	Peak collector current	15	A
I _C	Collector current	8	A
P _C	Collector power dissipation	30	W
T _j	Junction temperature	150	°C
T _{stg}	Storage temperature	-65~150	°C



TO-220F

◆ Electrical Characteristics Tc=25°C

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I _{CB0}	Collector cut-off current	V _{CB} =400V; I _E =0		0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0		3.5	mA
I _{CEO}	Collector cut-off current				
V _{CB0}	Collector-base breakdown voltage				
V _{CEO}	Collector-emitter Sustaining voltage	I _C =0.1A; I _B =0	200		V
V _{EBO}	Emitter-base breakdown voltage				
V _{CE(sat-1)}	Collector-emitter saturation voltages	I _C =5A; I _B =50mA		1.5	V
V _{CE(sat-2)}	Collector-emitter saturation voltages				
h _{FE-1}	Forward current transfer ratio	I _C =5A; V _{CE} =5V	200		
h _{FE-2}	Forward current transfer ratio				
V _{BE(sat)1}	Base-emitter saturation voltages	I _C =5A; I _B =50mA		2.4	V
V _{BE(sat)2}	Base-emitter saturation voltages				
V _F	Damper diode forward voltage	I _F =4A		2.0	V
f _T	Transition frequency at f=1MHz				